PROGRAM

	Monday 1st	Tuesday 2nd	Wednesday 3rd
09:00 - 09:30	Registration		
09:30 - 10:00	Openning	Poster Session	L. Errico
10:00 - 10:50	S. Bampi	Poster Session	F. Palumbo
10:50 - 11:20	Coffe Break		
11:20 – 12:10	F. Rubinelli	P. Levy	M. Alurralde
12:10 – 14:00	L U N C H		
14:00 – 14:50	J. Plá	F. Guarin (EDS)	E. Peltzer y Blancá
14:50 – 15:40	J. Piprek	E. Miranda (EDS)	V. Sverdlov
15:40 – 16:10	Coffe Break		
16:10 – 17:00	V. Ferraresi	M. Pavanello (EDS)	Closing Remarks
17:00 – 17:15			Closing Remarks

TECHNICAL PROGRAM

Monday 1st

9:00 Hs:	Registration
9:30 Hs:	Opening Session *Eitel L. Peltzer y Blancá*
10:00 Hs:	Nano-CMOS at the end of the 2-D scaling: The role of FinFETs on Silicon nanowires *Sergio Bampi (UFRGS, Brazil)*
10:50 Hs:	Coffee Break
11:20 Hs:	Computer Modelling of Hydrogenated Amorphous and Microcrystalline Silicon Based Solar Cells *Francisco Rubinelli (INTEC-UNL, CONICET, Argentina)*
12:10 Hs:	Lunch
14:00 Hs:	Simulation of PV Devices at CNEA. Optical Properties of Solar Cell Structures, Homojunction and Multijunction Solar Cells, and PV Arrays for Space Applications *Juan Plá (GES-CAC-CNEA, CONICET, Argentina)*
14:50 Hs:	Impact of Nitride Material Properties on the Performance of GaN-based Light Emitters *Joachim Piprek (NUSOD Institute LLC, USA)*
15:40 Hs:	Coffee Break
16:10 Hs:	B3LYP/cc-pVTZ Study on Small Binary AlnPm ($n = 1\text{-}4$, $m = 1\text{-}4$; $n + m \leq 5$) Clusters *Verónica Ferraresi Curotto (CEQUINOR-UNLP, CONICET, Argentina) (Best Student Paper)*

Tuesday 2nd

9:30 Hs: Poster Session

Degradation dynamics of Al/$HfYO_x$/GaAs structures with and without an interfacial passivation layer
E. Miranda, C. Mahata, T. Das, C.K. Maiti

Electrooptical Properties of GeTe for Phase Change Memory
M.V. Walz

Alkane thiol and dithiol films grown on GaAs and InP under UHV conditions
L.J. Salazar Alarcón, L.J. Cristina, E.A. Sánchez, J.E. Gayone, O. Grizzi

Electron and ion conduction of poly(*o*-aminophenol) in the presence of sulfate and benzenesulfonate anions
R. Tucceri

Application of an Electro-Optical Model for Organic Solar Cells Based on the Principle of Detailed Balance
M. Soldera, K. Taretto, T. Kirchartz

Analysis and design of a four-stage CML ring oscillator based on MOS technology for use in fiber optic transceivers
E. Paulucci, L. Gimenez

Hydrogen storage in lithium hydrides. A first -principles study
R. Napán, E.L. Peltzer y Blancá

Electron conduction across nickel hydroxide deposited on glassy carbon electrodes
D. Posadas, R. Tucceri

10:50 Hs: Coffee Break

11:20 Hs: Resistive switching nonvolatile memory devices
Pablo Levy (GMC-CAC-CNEA, CONICET, Argentina)

12:10 Hs: Lunch

IEEE EDS 2010 MINI-COLLOQUIUM

14:00 Hs:	Semiconductor Reliability Topics for Advanced CMOS Technologies *Fernando Guarín (IBM Microelectronics, USA)*
14:50 Hs:	Analysis of the breakdown spots location in MOS structures using spatial statistics *Enrique Miranda (ETSE-UAB, Spain)*
15:40 Hs:	Coffee Break
16:10 Hs:	Impact of Device Architecture on the Analog Performance of Planar and Multiple Gate SOI MOSFETs *Marcelo Pavanello (FEI, Brazil)*

Wednesday 3rd

9:30 Hs:	Local structure around Fe impurities in rutile TiO_2 *Leonardo Errico (IFLP, UNLP, CONICET, UNNOBA, Argentina)*
10:00 Hs:	Progressive Breakdown: Structure of the Oxide Damage and Reliability Projection *Félix Palumbo (CONICET, CAC-CNEA, UTN, Argentina)*
10:50 Hs:	Coffee Break
11:20 Hs:	Applying Simulation to Radiation Effects characterization of Electronic Devices, The Solar Cells case *Martín Alurralde (GES-CAC-CNEA, UNSAM, Argentina)*
12:10 Hs:	Lunch
14:00 Hs:	A brief story about a very important tool, g'-Fe4N : simple and complex magnetic material *Eitel Peltzer y Blancá (GEMyDE-FI-UNLP, IFLYSIB-CONICET-UNLP, Argentina)*
14:50 Hs:	Modeling of Modern MOSFETs with Strain *Victor Sverdlov (TUWIEN, Austria)*
15:40 Hs:	Coffee Break
16:10 Hs:	Closing Remarks